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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	50MHz
Connectivity	I ² C, IrDA, SPI, UART/USART
Peripherals	DMA, I ² S, LVD, POR, PWM, WDT
Number of I/O	44
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 19x16b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mk10dx128vlh5

1 Ordering parts

1.1 Determining valid orderable parts

Valid orderable part numbers are provided on the web. To determine the orderable part numbers for this device, go to <http://www.freescale.com> and perform a part number search for the following device numbers: PK10 and MK10 .

2 Part identification

2.1 Description

Part numbers for the chip have fields that identify the specific part. You can use the values of these fields to determine the specific part you have received.

2.2 Format

Part numbers for this device have the following format:

Q K## A M FFF R T PP CC N

2.3 Fields

This table lists the possible values for each field in the part number (not all combinations are valid):

Field	Description	Values
Q	Qualification status	<ul style="list-style-type: none"> M = Fully qualified, general market flow P = Prequalification
K##	Kinetis family	<ul style="list-style-type: none"> K10
A	Key attribute	<ul style="list-style-type: none"> D = Cortex-M4 w/ DSP F = Cortex-M4 w/ DSP and FPU
M	Flash memory type	<ul style="list-style-type: none"> N = Program flash only X = Program flash and FlexMemory

Table continues on the next page...

3.1 Definition: Operating requirement

An *operating requirement* is a specified value or range of values for a technical characteristic that you must guarantee during operation to avoid incorrect operation and possibly decreasing the useful life of the chip.

3.1.1 Example

This is an example of an operating requirement, which you must meet for the accompanying operating behaviors to be guaranteed:

Symbol	Description	Min.	Max.	Unit
V _{DD}	1.0 V core supply voltage	0.9	1.1	V

3.2 Definition: Operating behavior

An *operating behavior* is a specified value or range of values for a technical characteristic that are guaranteed during operation if you meet the operating requirements and any other specified conditions.

3.2.1 Example

This is an example of an operating behavior, which is guaranteed if you meet the accompanying operating requirements:

Symbol	Description	Min.	Max.	Unit
I _{WP}	Digital I/O weak pullup/pulldown current	10	130	μA

3.3 Definition: Attribute

An *attribute* is a specified value or range of values for a technical characteristic that are guaranteed, regardless of whether you meet the operating requirements.

3.3.1 Example

This is an example of an attribute:

Symbol	Description	Min.	Max.	Unit
CIN_D	Input capacitance: digital pins	—	7	pF

3.4 Definition: Rating

A *rating* is a minimum or maximum value of a technical characteristic that, if exceeded, may cause permanent chip failure:

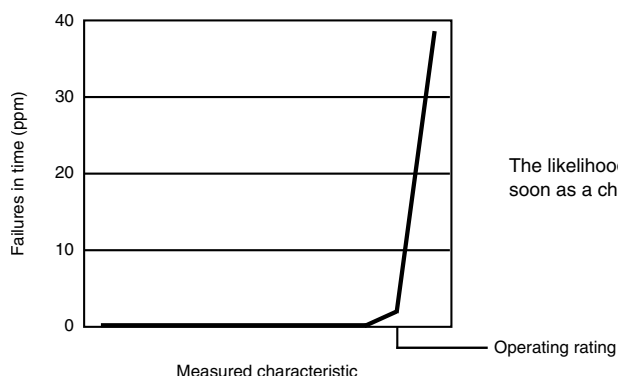
- *Operating ratings* apply during operation of the chip.
- *Handling ratings* apply when the chip is not powered.

3.4.1 Example

This is an example of an operating rating:

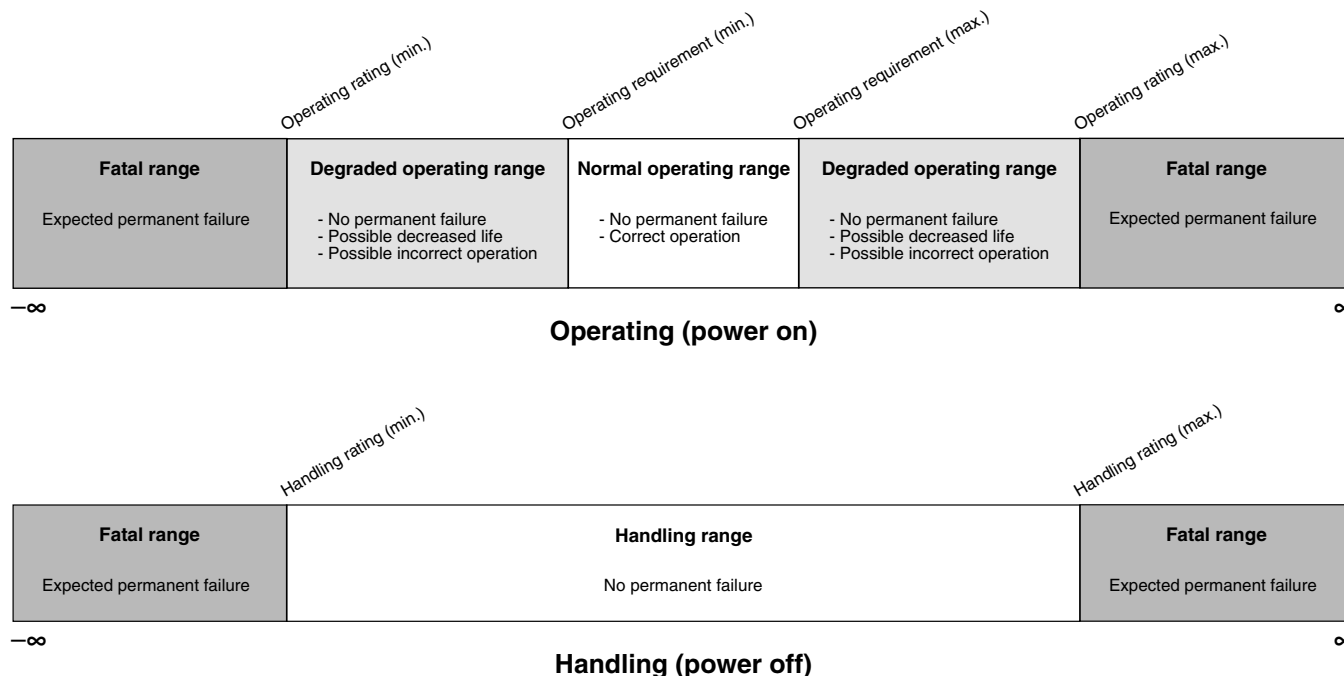
Symbol	Description	Min.	Max.	Unit
V _{DD}	1.0 V core supply voltage	−0.3	1.2	V

3.5 Result of exceeding a rating



The likelihood of permanent chip failure increases rapidly as soon as a characteristic begins to exceed one of its operating ratings.

3.6 Relationship between ratings and operating requirements



3.7 Guidelines for ratings and operating requirements

Follow these guidelines for ratings and operating requirements:

- Never exceed any of the chip's ratings.
- During normal operation, don't exceed any of the chip's operating requirements.
- If you must exceed an operating requirement at times other than during normal operation (for example, during power sequencing), limit the duration as much as possible.

3.8 Definition: Typical value

A *typical value* is a specified value for a technical characteristic that:

- Lies within the range of values specified by the operating behavior
- Given the typical manufacturing process, is representative of that characteristic during operation when you meet the typical-value conditions or other specified conditions

Typical values are provided as design guidelines and are neither tested nor guaranteed.

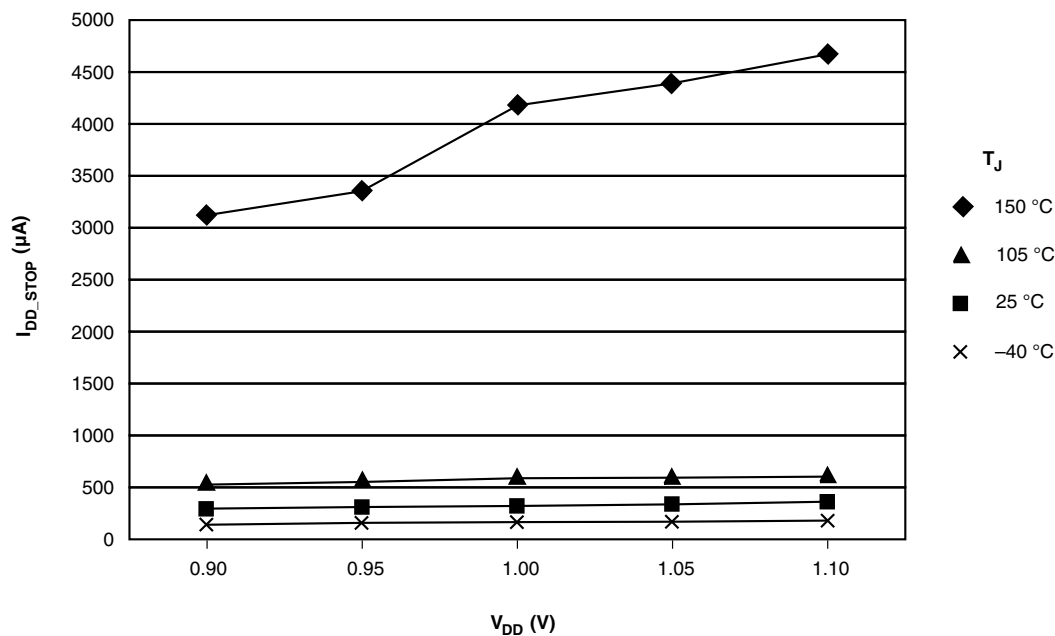
3.8.1 Example 1

This is an example of an operating behavior that includes a typical value:

Symbol	Description	Min.	Typ.	Max.	Unit
I_{WP}	Digital I/O weak pullup/pulldown current	10	70	130	μA

3.8.2 Example 2

This is an example of a chart that shows typical values for various voltage and temperature conditions:



3.9 Typical value conditions

Typical values assume you meet the following conditions (or other conditions as specified):

Symbol	Description	Value	Unit
T_A	Ambient temperature	25	°C
V_{DD}	3.3 V supply voltage	3.3	V

Table 5. Power mode transition operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
t_{POR}	After a POR event, amount of time from the point V_{DD} reaches 1.71 V to execution of the first instruction across the operating temperature range of the chip.	—	300	μs	1
	• VLLS0 → RUN	—	130	μs	
	• VLLS1 → RUN	—	130	μs	
	• VLLS2 → RUN	—	70	μs	
	• VLLS3 → RUN	—	70	μs	
	• LLS → RUN	—	6	μs	
	• VLPS → RUN	—	5.2	μs	
	• STOP → RUN	—	5.2	μs	

1. Normal boot (FTFL_OPT[LPBOOT]=1)

5.2.5 Power consumption operating behaviors

Table 6. Power consumption operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DDA}	Analog supply current	—	—	See note	mA	1
I_{DD_RUN}	Run mode current — all peripheral clocks disabled, code executing from flash	—	13.7	15.1	mA	2
		—	13.9	15.3	mA	
I_{DD_RUN}	Run mode current — all peripheral clocks enabled, code executing from flash	—	16.1	18.2	mA	3, 4
		—	16.3	17.7	mA	
		—	16.7	18.4	mA	
		—	16.7	18.4	mA	
I_{DD_WAIT}	Wait mode high frequency current at 3.0 V — all peripheral clocks disabled	—	7.5	8.4	mA	2
I_{DD_WAIT}	Wait mode reduced frequency current at 3.0 V — all peripheral clocks disabled	—	5.6	6.4	mA	5

Table continues on the next page...

emission level is the value of the maximum measured emission, rounded up to the next whole number, from among the measured orientations in each frequency range.

2. $V_{DD} = 3.3\text{ V}$, $T_A = 25\text{ }^{\circ}\text{C}$, $f_{OSC} = 12\text{ MHz}$ (crystal), $f_{SYS} = 48\text{ MHz}$, $f_{BUS} = 48\text{ MHz}$
3. Specified according to Annex D of IEC Standard 61967-2, *Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*

5.2.7 Designing with radiated emissions in mind

To find application notes that provide guidance on designing your system to minimize interference from radiated emissions:

1. Go to <http://www.freescale.com>.
2. Perform a keyword search for “EMC design.”

5.2.8 Capacitance attributes

Table 8. Capacitance attributes

Symbol	Description	Min.	Max.	Unit
C_{IN_A}	Input capacitance: analog pins	—	7	pF
C_{IN_D}	Input capacitance: digital pins	—	7	pF

5.3 Switching specifications

5.3.1 Device clock specifications

Table 9. Device clock specifications

Symbol	Description	Min.	Max.	Unit	Notes
Normal run mode					
f_{SYS}	System and core clock	—	50	MHz	
f_{BUS}	Bus clock	—	50	MHz	
f_{FLASH}	Flash clock	—	25	MHz	
f_{LPTMR}	LPTMR clock	—	25	MHz	
VLPR mode ¹					
f_{SYS}	System and core clock	—	4	MHz	
f_{BUS}	Bus clock	—	4	MHz	
f_{FLASH}	Flash clock	—	1	MHz	
f_{ERCLK}	External reference clock	—	16	MHz	

Table continues on the next page...

Table 9. Device clock specifications (continued)

Symbol	Description	Min.	Max.	Unit	Notes
$f_{\text{LPTMR_pin}}$	LPTMR clock	—	25	MHz	
$f_{\text{LPTMR_ERCLK}}$	LPTMR external reference clock	—	16	MHz	
$f_{\text{I2S_MCLK}}$	I2S master clock	—	12.5	MHz	
$f_{\text{I2S_BCLK}}$	I2S bit clock	—	4	MHz	

1. The frequency limitations in VLPR mode here override any frequency specification listed in the timing specification for any other module.

5.3.2 General switching specifications

These general purpose specifications apply to all signals configured for GPIO, UART, CMT, and I²C signals.

Table 10. General switching specifications

Symbol	Description	Min.	Max.	Unit	Notes
	GPIO pin interrupt pulse width (digital glitch filter disabled) — Synchronous path	1.5	—	Bus clock cycles	1, 2
	GPIO pin interrupt pulse width (digital glitch filter disabled, analog filter enabled) — Asynchronous path	100	—	ns	3
	GPIO pin interrupt pulse width (digital glitch filter disabled, analog filter disabled) — Asynchronous path	50	—	ns	3
	External reset pulse width (digital glitch filter disabled)	100	—	ns	3
	Mode select ($\overline{\text{EZP_CS}}$) hold time after reset deassertion	2	—	Bus clock cycles	
	Port rise and fall time (high drive strength) <ul style="list-style-type: none"> Slew disabled <ul style="list-style-type: none"> $1.71 \leq V_{\text{DD}} \leq 2.7\text{V}$ $2.7 \leq V_{\text{DD}} \leq 3.6\text{V}$ Slew enabled <ul style="list-style-type: none"> $1.71 \leq V_{\text{DD}} \leq 2.7\text{V}$ $2.7 \leq V_{\text{DD}} \leq 3.6\text{V}$ 	— — — —	13 7 36 24	ns ns ns ns	4

Table continues on the next page...

Peripheral operating requirements and behaviors

Board type	Symbol	Description	64 MAPBGA	64 LQFP	Unit	Notes
Single-layer (1s)	$R_{\theta JA}$	Thermal resistance, junction to ambient (200 ft./min. air speed)	90	53	°C/W	1,3
Four-layer (2s2p)	$R_{\theta JA}$	Thermal resistance, junction to ambient (200 ft./min. air speed)	51	40	°C/W	,
—	$R_{\theta JB}$	Thermal resistance, junction to board	31	28	°C/W	5
—	$R_{\theta JC}$	Thermal resistance, junction to case	31	15	°C/W	6
—	Ψ_{JT}	Thermal characterization parameter, junction to package top outside center (natural convection)	6	3	°C/W	7

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
2. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air)* with the single layer board horizontal. For the LQFP, the board meets the JESD51-3 specification. For the MAPBGA, the board meets the JESD51-9 specification.
3. Determined according to JEDEC Standard JESD51-6, *Integrated Circuits Thermal Test Method Environmental Conditions—Forced Convection (Moving Air)* with the board horizontal.
5. Determined according to JEDEC Standard JESD51-8, *Integrated Circuit Thermal Test Method Environmental Conditions—Junction-to-Board*. Board temperature is measured on the top surface of the board near the package.
6. Determined according to Method 1012.1 of MIL-STD 883, *Test Method Standard, Microcircuits*, with the cold plate temperature used for the case temperature. The value includes the thermal resistance of the interface material between the top of the package and the cold plate.
7. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air)*.

6 Peripheral operating requirements and behaviors

6.1 Core modules

6.1.1 JTAG electricals

Table 12. JTAG voltage range electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	2.7	5.5	V
J1	TCLK frequency of operation <ul style="list-style-type: none"> • JTAG • CJTAG 	— —	10 5	MHz
J2	TCLK cycle period	1/J1	—	ns
J3	TCLK clock pulse width <ul style="list-style-type: none"> • JTAG • CJTAG 	100 200	— —	ns ns ns
J4	TCLK rise and fall times	—	1	ns
J5	TMS input data setup time to TCLK rise <ul style="list-style-type: none"> • JTAG • CJTAG 	53 112	— —	ns
J6	TDI input data setup time to TCLK rise	8	—	ns
J7	TMS input data hold time after TCLK rise <ul style="list-style-type: none"> • JTAG • CJTAG	3.4 3.4	— —	ns
J8	TDI input data hold time after TCLK rise	3.4	—	ns
J9	TCLK low to TMS data valid <ul style="list-style-type: none"> • JTAG • CJTAG 	— —	48 85	ns
J10	TCLK low to TDO data valid	—	48	ns
J11	Output data hold/invalid time after clock edge ¹	—	3	ns

1. They are common for JTAG and CJTAG. Input transition = 1 ns and Output load = 50pf

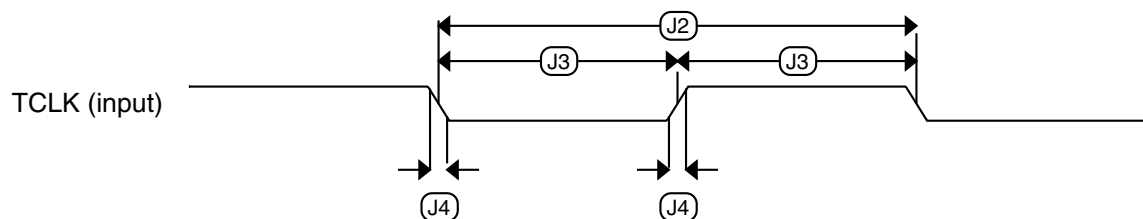


Figure 4. Test clock input timing

Table 13. MCG specifications (continued)

Symbol	Description		Min.	Typ.	Max.	Unit	Notes
f _{fill_ref}	FLL reference frequency range		31.25	—	39.0625	kHz	
f _{dco}	DCO output frequency range	Low range (DRS=00) 640 × f _{fill_ref}	20	20.97	25	MHz	2, 3
		Mid range (DRS=01) 1280 × f _{fill_ref}	40	41.94	50	MHz	
		Mid-high range (DRS=10) 1920 × f _{fill_ref}	60	62.91	75	MHz	
		High range (DRS=11) 2560 × f _{fill_ref}	80	83.89	100	MHz	
f _{dco_t_DMx3} 2	DCO output frequency	Low range (DRS=00) 732 × f _{fill_ref}	—	23.99	—	MHz	4, 5
		Mid range (DRS=01) 1464 × f _{fill_ref}	—	47.97	—	MHz	
		Mid-high range (DRS=10) 2197 × f _{fill_ref}	—	71.99	—	MHz	
		High range (DRS=11) 2929 × f _{fill_ref}	—	95.98	—	MHz	
J _{cyc_fill}	FLL period jitter <ul style="list-style-type: none">f_{VCO} = 48 MHzf_{VCO} = 98 MHz		— —	180 150	— —	ps	
t _{fill_acquire}	FLL target frequency acquisition time		—	—	1	ms	6
PLL							
f _{vco}	VCO operating frequency		48.0	—	100	MHz	
I _{pll}	PLL operating current <ul style="list-style-type: none">PLL @ 96 MHz (f_{osc_hi_1} = 8 MHz, f_{pll_ref} = 2 MHz, VDIV multiplier = 48)		—	1060	—	μA	7
I _{pll}	PLL operating current <ul style="list-style-type: none">PLL @ 48 MHz (f_{osc_hi_1} = 8 MHz, f_{pll_ref} = 2 MHz, VDIV multiplier = 24)		—	600	—	μA	7
f _{pll_ref}	PLL reference frequency range		2.0	—	4.0	MHz	
J _{cyc_pll}	PLL period jitter (RMS)						8
	<ul style="list-style-type: none">f_{vco} = 48 MHzf_{vco} = 100 MHz		— —	120 50	— —	ps ps	

Table continues on the next page...

Table 19. Flash command timing specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
Word-write to FlexRAM for EEPROM operation						
$t_{\text{eewr16bers}}$	Word-write to erased FlexRAM location execution time	—	175	260	μs	
$t_{\text{eewr16b8k}}$	Word-write to FlexRAM execution time: • 8 KB EEPROM backup	—	340	1700	μs	
$t_{\text{eewr16b16k}}$	• 16 KB EEPROM backup	—	385	1800	μs	
$t_{\text{eewr16b32k}}$	• 32 KB EEPROM backup	—	475	2000	μs	
Longword-write to FlexRAM for EEPROM operation						
$t_{\text{eewr32bers}}$	Longword-write to erased FlexRAM location execution time	—	360	540	μs	
$t_{\text{eewr32b8k}}$	Longword-write to FlexRAM execution time: • 8 KB EEPROM backup	—	545	1950	μs	
$t_{\text{eewr32b16k}}$	• 16 KB EEPROM backup	—	630	2050	μs	
$t_{\text{eewr32b32k}}$	• 32 KB EEPROM backup	—	810	2250	μs	

1. Assumes 25MHz flash clock frequency.
2. Maximum times for erase parameters based on expectations at cycling end-of-life.
3. For byte-writes to an erased FlexRAM location, the aligned word containing the byte must be erased.

6.4.1.3 Flash high voltage current behaviors

Table 20. Flash high voltage current behaviors

Symbol	Description	Min.	Typ.	Max.	Unit
$I_{\text{DD_PGM}}$	Average current adder during high voltage flash programming operation	—	2.5	6.0	mA
$I_{\text{DD_ERS}}$	Average current adder during high voltage flash erase operation	—	1.5	4.0	mA

6.4.1.4 Reliability specifications

Table 21. NVM reliability specifications

Symbol	Description	Min.	Typ. ¹	Max.	Unit	Notes
Program Flash						
$t_{\text{nv mretp10k}}$	Data retention after up to 10 K cycles	5	50	—	years	
$t_{\text{nv mretp1k}}$	Data retention after up to 1 K cycles	20	100	—	years	
$n_{\text{nv mcycp}}$	Cycling endurance	10 K	50 K	—	cycles	2
Data Flash						
$t_{\text{nv mretd10k}}$	Data retention after up to 10 K cycles	5	50	—	years	

Table continues on the next page...

- EEPROM — allocated FlexNVM based on DEPART; entered with the Program Partition command
- EEESIZE — allocated FlexRAM based on DEPART; entered with the Program Partition command
- Write_efficiency —
 - 0.25 for 8-bit writes to FlexRAM
 - 0.50 for 16-bit or 32-bit writes to FlexRAM
- n_{nvmcycd} — data flash cycling endurance (the following graph assumes 10,000 cycles)

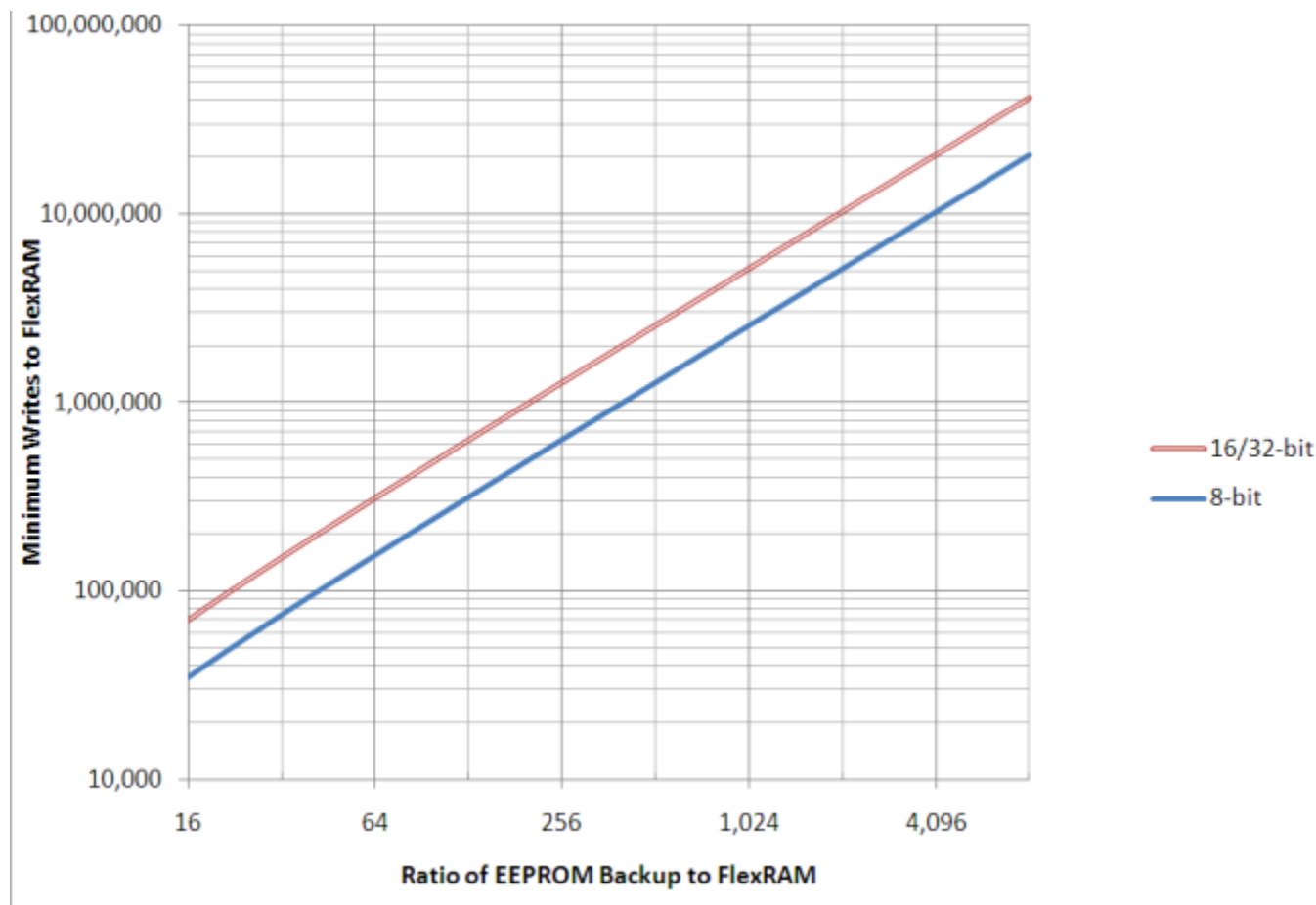


Figure 8. EEPROM backup writes to FlexRAM

6.4.2 EzPort Switching Specifications

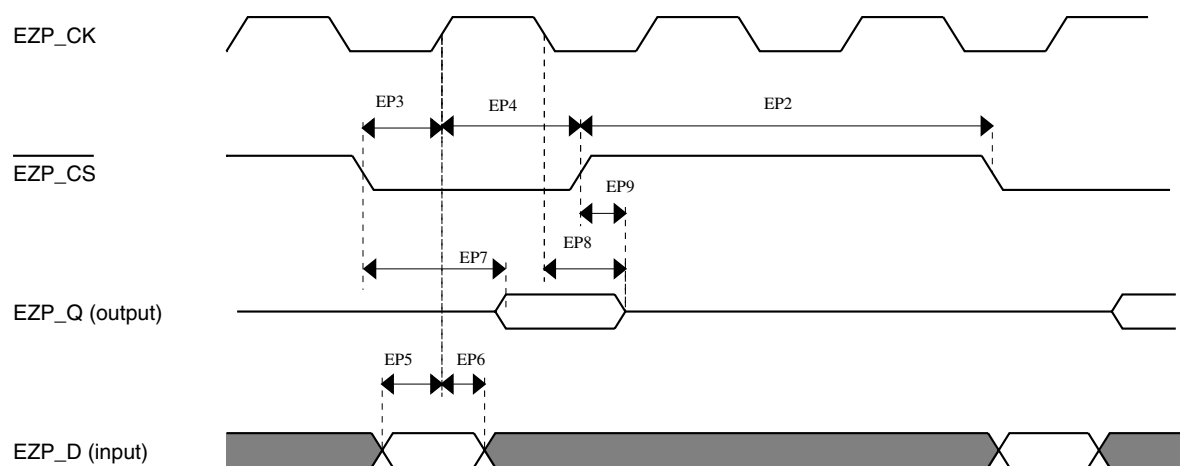
Table 22. EzPort switching specifications

Num	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V

Table continues on the next page...

Table 22. EzPort switching specifications (continued)

Num	Description	Min.	Max.	Unit
EP1	EZP_CK frequency of operation (all commands except READ)	—	$f_{\text{SYS}}/2$	MHz
EP1a	EZP_CK frequency of operation (READ command)	—	$f_{\text{SYS}}/8$	MHz
EP2	$\overline{\text{EZP_CS}}$ negation to next $\overline{\text{EZP_CS}}$ assertion	$2 \times t_{\text{EZP_CK}}$	—	ns
EP3	$\overline{\text{EZP_CS}}$ input valid to EZP_CK high (setup)	5	—	ns
EP4	EZP_CK high to $\overline{\text{EZP_CS}}$ input invalid (hold)	5	—	ns
EP5	EZP_D input valid to EZP_CK high (setup)	2	—	ns
EP6	EZP_CK high to EZP_D input invalid (hold)	5	—	ns
EP7	EZP_CK low to EZP_Q output valid	—	17	ns
EP8	EZP_CK low to EZP_Q output invalid (hold)	0	—	ns
EP9	$\overline{\text{EZP_CS}}$ negation to EZP_Q tri-state	—	12	ns

**Figure 9. EzPort Timing Diagram**

6.5 Security and integrity modules

There are no specifications necessary for the device's security and integrity modules.

6.6 Analog

6.6.1 ADC electrical specifications

The 16-bit accuracy specifications listed in [Table 23](#) and [Table 24](#) are achievable on the differential pins ADCx_DP0, ADCx_DM0.

All other ADC channels meet the 13-bit differential/12-bit single-ended accuracy specifications.

6.6.1.1 16-bit ADC operating conditions

Table 23. 16-bit ADC operating conditions

Symbol	Description	Conditions	Min.	Typ. ¹	Max.	Unit	Notes
V _{DDA}	Supply voltage	Absolute	1.71	—	3.6	V	
ΔV _{DDA}	Supply voltage	Delta to V _{DD} (V _{DD} - V _{DDA})	-100	0	+100	mV	2
ΔV _{SSA}	Ground voltage	Delta to V _{SS} (V _{SS} - V _{SSA})	-100	0	+100	mV	2
V _{REFH}	ADC reference voltage high		1.13	V _{DDA}	V _{DDA}	V	
V _{REFL}	Reference voltage low		V _{SSA}	V _{SSA}	V _{SSA}	V	
V _{ADIN}	Input voltage		V _{REFL}	—	V _{REFH}	V	
C _{ADIN}	Input capacitance	<ul style="list-style-type: none"> 16 bit modes 8/10/12 bit modes 	— —	8 4	10 5	pF	
R _{ADIN}	Input resistance		—	2	5	kΩ	
R _{AS}	Analog source resistance	13/12 bit modes f _{ADCK} < 4MHz	—	—	5	kΩ	3
f _{ADCK}	ADC conversion clock frequency	≤ 13 bit modes	1.0	—	18.0	MHz	4
f _{ADCK}	ADC conversion clock frequency	16 bit modes	2.0	—	12.0	MHz	4
C _{rate}	ADC conversion rate	≤ 13 bit modes No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	20.000	—	818.330	Ksps	5

Table continues on the next page...

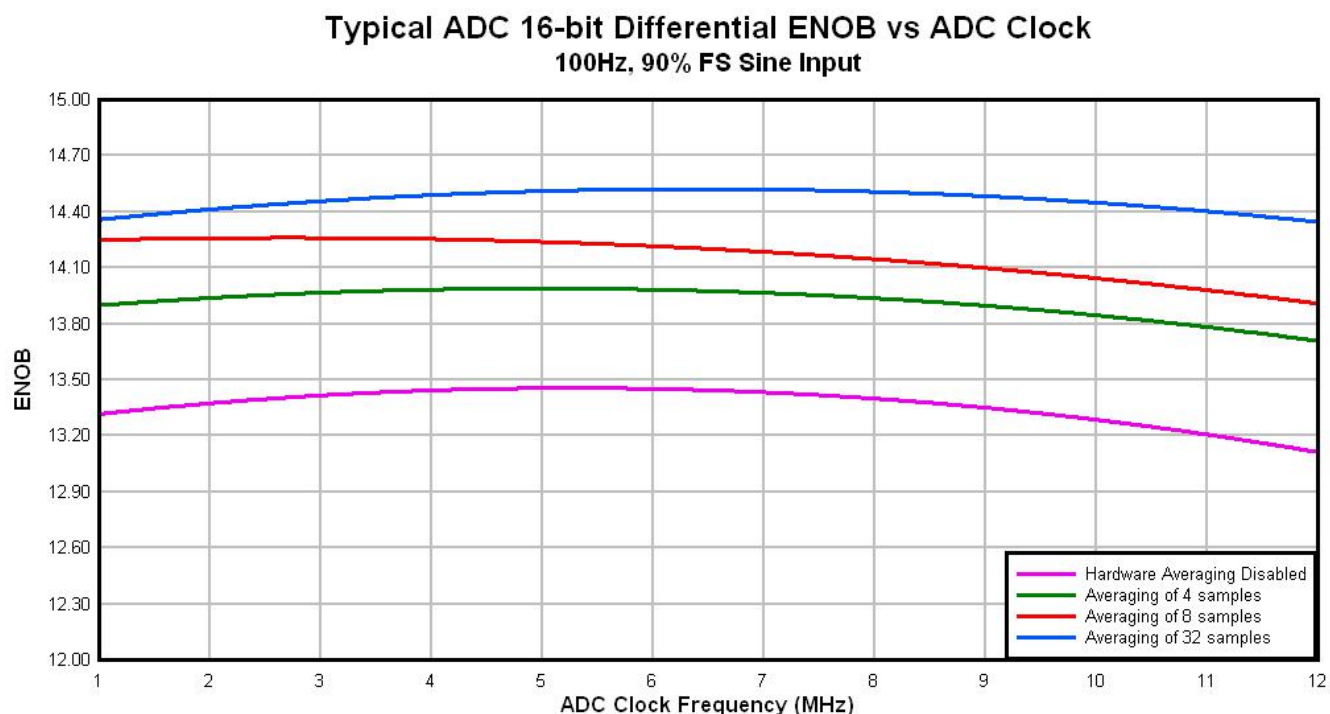


Figure 11. Typical ENOB vs. ADC_CLK for 16-bit differential mode

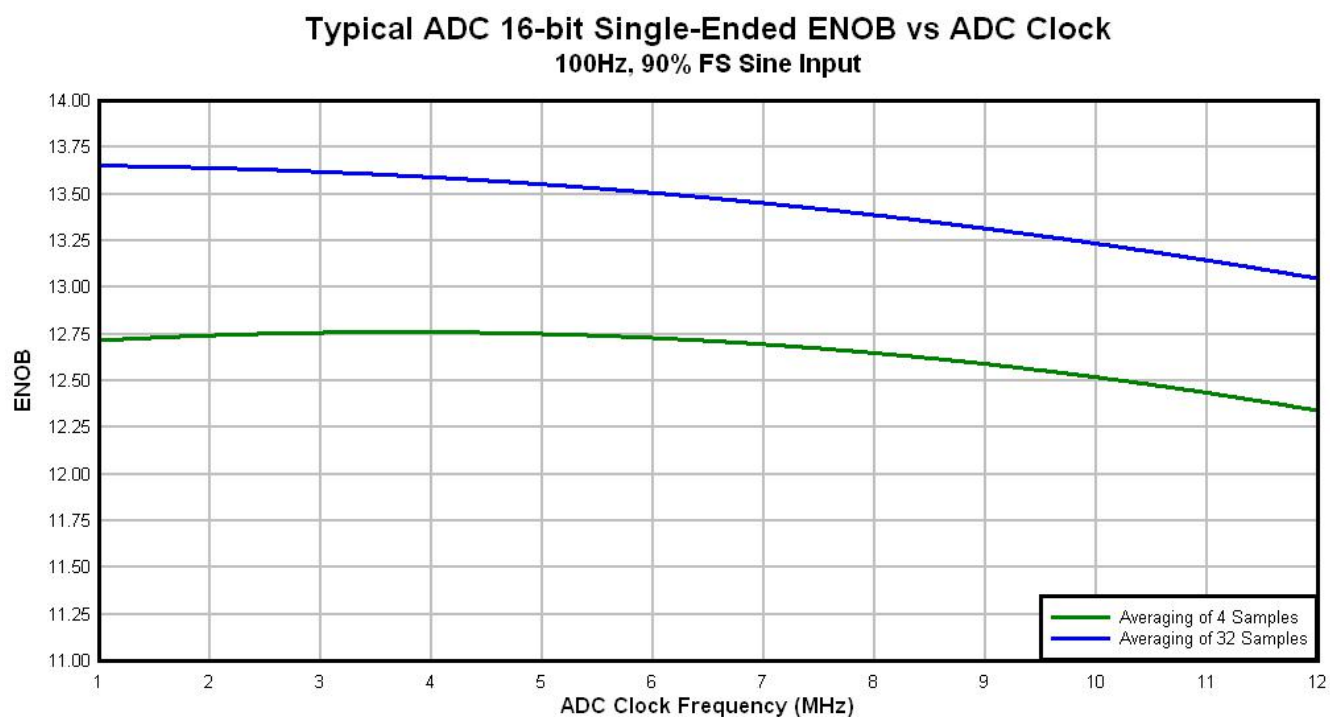


Figure 12. Typical ENOB vs. ADC_CLK for 16-bit single-ended mode

6.6.2 CMP and 6-bit DAC electrical specifications

Table 25. Comparator and 6-bit DAC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit
V_{DD}	Supply voltage	1.71	—	3.6	V
I_{DDHS}	Supply current, High-speed mode (EN=1, PMODE=1)	—	—	200	μ A
$I_{DDL S}$	Supply current, low-speed mode (EN=1, PMODE=0)	—	—	20	μ A
V_{AIN}	Analog input voltage	$V_{SS} - 0.3$	—	V_{DD}	V
V_{AIO}	Analog input offset voltage	—	—	20	mV
V_H	Analog comparator hysteresis ¹				
	• CR0[HYSTCTR] = 00	—	5	—	mV
	• CR0[HYSTCTR] = 01	—	10	—	mV
	• CR0[HYSTCTR] = 10	—	20	—	mV
	• CR0[HYSTCTR] = 11	—	30	—	mV
V_{CMPOH}	Output high	$V_{DD} - 0.5$	—	—	V
V_{CMPOI}	Output low	—	—	0.5	V
t_{DHS}	Propagation delay, high-speed mode (EN=1, PMODE=1)	20	50	200	ns
t_{DLS}	Propagation delay, low-speed mode (EN=1, PMODE=0)	80	250	600	ns
	Analog comparator initialization delay ²	—	—	40	μ s
I_{DAC6b}	6-bit DAC current adder (enabled)	—	7	—	μ A
INL	6-bit DAC integral non-linearity	−0.5	—	0.5	LSB ³
DNL	6-bit DAC differential non-linearity	−0.3	—	0.3	LSB

1. Typical hysteresis is measured with input voltage range limited to 0.6 to $V_{DD}-0.6V$.

2. Comparator initialization delay is defined as the time between software writes to change control inputs (Writes to DACEN, VRSEL, PSEL, MSEL, VOSEL) and the comparator output settling to a stable level.

3. 1 LSB = $V_{reference}/64$

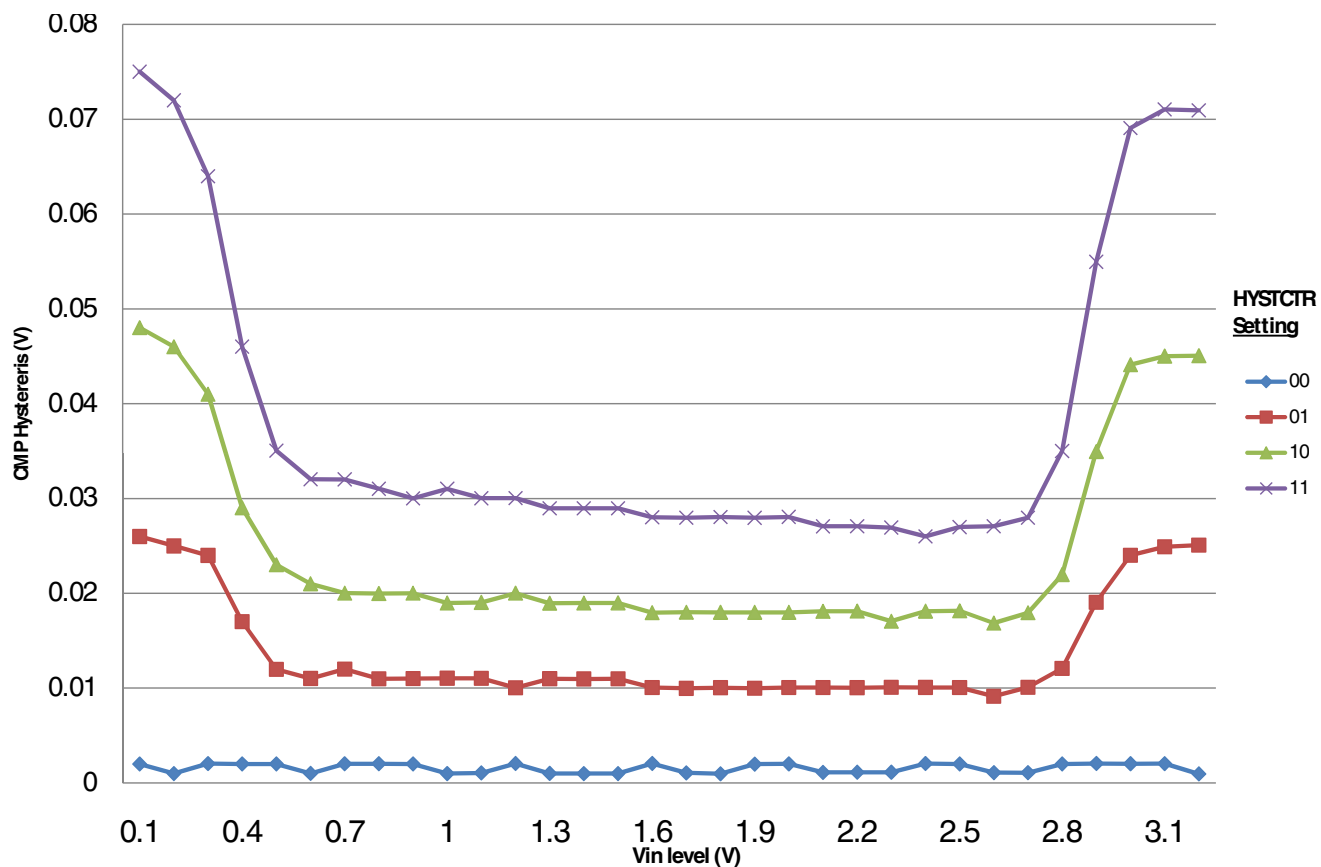
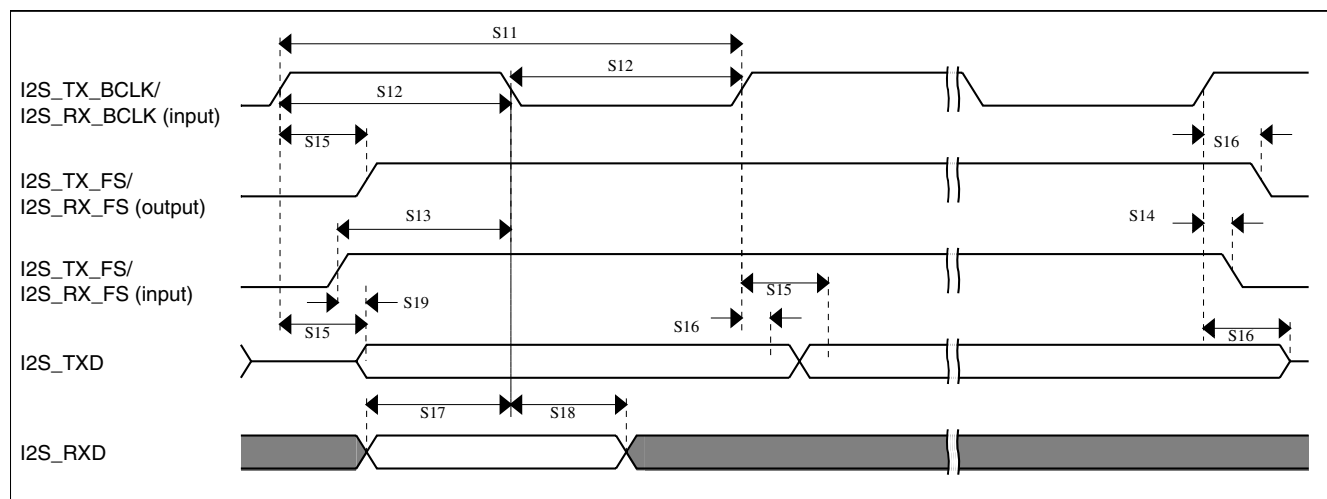


Figure 13. Typical hysteresis vs. Vin level (VDD=3.3V, PMODE=0)

Table 37. I2S/SAI slave mode timing in VLPR, VLPW, and VLPS modes (full voltage range) (continued)

Num.	Characteristic	Min.	Max.	Unit
S12	I2S_TX_BCLK/I2S_RX_BCLK pulse width high/low (input)	45%	55%	MCLK period
S13	I2S_TX_FS/I2S_RX_FS input setup before I2S_TX_BCLK/I2S_RX_BCLK	30	—	ns
S14	I2S_TX_FS/I2S_RX_FS input hold after I2S_TX_BCLK/I2S_RX_BCLK	3	—	ns
S15	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output valid	—	63	ns
S16	I2S_TX_BCLK to I2S_TXD/I2S_TX_FS output invalid	0	—	ns
S17	I2S_RXD setup before I2S_RX_BCLK	30	—	ns
S18	I2S_RXD hold after I2S_RX_BCLK	2	—	ns
S19	I2S_TX_FS input assertion to I2S_TXD output valid ¹	—	72	ns

1. Applies to first bit in each frame and only if the TCR4[FSE] bit is clear

**Figure 22. I2S/SAI timing — slave modes**

6.9 Human-machine interfaces (HMI)

6.9.1 TSI electrical specifications

Table 38. TSI electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V _{DDTSI}	Operating voltage	1.71	—	3.6	V	
C _{ELE}	Target electrode capacitance range	1	20	500	pF	1

Table continues on the next page...

7 Dimensions

7.1 Obtaining package dimensions

Package dimensions are provided in package drawings.

To find a package drawing, go to <http://www.freescale.com> and perform a keyword search for the drawing's document number:

If you want the drawing for this package	Then use this document number
64-pin LQFP	98ASS23234W
64-pin MAPBGA	98ASA00420D

8 Pinout

8.1 K10 Signal Multiplexing and Pin Assignments

The following table shows the signals available on each pin and the locations of these pins on the devices supported by this document. The Port Control Module is responsible for selecting which ALT functionality is available on each pin.

64 MAP BGA	64 LQFP	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EzPort
A1	1	PTE0	DISABLED		PTE0		UART1_TX				RTC_CLKOUT	
B1	2	PTE1/ LLWU_P0	DISABLED		PTE1/ LLWU_P0		UART1_RX					
C5	3	VDD	VDD	VDD								
C4	4	VSS	VSS	VSS								
E1	5	PTE16	ADC0_SE4a	ADC0_SE4a	PTE16	SPI0_PCS0	UART2_TX	FTM_CLKIN0		FTM0_FLT3		
D1	6	PTE17	ADC0_SE5a	ADC0_SE5a	PTE17	SPI0_SCK	UART2_RX	FTM_CLKIN1		LPTMR0_ALT3		
E2	7	PTE18	ADC0_SE6a	ADC0_SE6a	PTE18	SPI0_SOUT	UART2_CTS_b	I2C0_SDA				
D2	8	PTE19	ADC0_SE7a	ADC0_SE7a	PTE19	SPI0_SIN	UART2_RTS_b	I2C0_SCL				
G1	9	ADC0_DP0	ADC0_DP0	ADC0_DP0								
F1	10	ADC0_DM0	ADC0_DM0	ADC0_DM0								
G2	11	ADC0_DP3	ADC0_DP3	ADC0_DP3								